Patrick Berwian

List of Publications by Year
in descending order

33	548	840119 11	713013 21
papers	citations	h-index	g-index

34	34	34	501
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Formation of CuInSe2 by the annealing of stacked elemental layersâ€"analysis by in situ high-energy powder diffraction. Thin Solid Films, 2003, 437, 297-307.	0.8	86
2	Fabrication and nanophotonic waveguide integration of silicon carbide colour centres with preserved spin-optical coherence. Nature Materials, 2022, 21, 67-73.	13.3	80
3	Laser Writing of Scalable Single Color Centers in Silicon Carbide. Nano Letters, 2019, 19, 2377-2383.	4.5	70
4	Threading dislocations in n- and p-type 4Hâ€"SiC material analyzed by etching and synchrotron X-ray topography. Journal of Crystal Growth, 2011, 314, 21-29.	0.7	45
5	Kinetics of the reactive crystallization of CuInSe2 and CuGaSe2 chalcopyrite films for solar cell applications. Journal of Crystal Growth, 2006, 287, 408-413.	0.7	37
6	Phase relations in the ternary Cuâ€"Gaâ€"In system. Thin Solid Films, 2007, 515, 5895-5898.	0.8	31
7	Low-pressure solution growth (LPSG) of GaN templates with diameters up to 3 inch. Journal of Crystal Growth, 2008, 310, 738-747.	0.7	22
8	Step-controlled homoepitaxial growth of 4Hâ€"SiC on vicinal substrates. Journal of Crystal Growth, 2013, 381, 127-133.	0.7	21
9	Selective etching of dislocations in GaN grown by low-pressure solution growth. Journal of Crystal Growth, 2010, 312, 3040-3045.	0.7	14
10	Imaging Defect Luminescence of 4H-SiC by Ultraviolet-Photoluminescence. Solid State Phenomena, 0, 242, 484-489.	0.3	14
11	Application of a thermogravimetric technique for the determination of low nitrogen solubilities in metals: Using iron as an example. Thermochimica Acta, 2008, 474, 36-40.	1.2	12
12	In situ resistivity measurements of precursor reactions in the Cuâ€"Inâ€"Ga system. Thin Solid Films, 2003, 431-432, 41-45.	0.8	11
13	Study on the kinetics of the formation reaction of GaN from Ga-solutions under ammonia atmosphere. Journal of Crystal Growth, 2007, 305, 326-334.	0.7	11
14	Dislocation Conversion and Propagation during Homoepitaxial Growth of 4H-SiC. Materials Science Forum, 0, 645-648, 299-302.	0.3	11
15	Doping induced lattice misfit in 4Hâ€"SiC homoepitaxy. Journal of Crystal Growth, 2012, 349, 43-49.	0.7	11
16	Experimental verification of the model by Klapper for 4H-SiC homoepitaxy on vicinal substrates. Journal of Applied Physics, 2013, 114, 183507.	1.1	9
17	Deeper insight into lifetime-engineering in 4H-SiC by ion implantation. Journal of Applied Physics, 2019, 126, .	1.1	9
18	Considerations on facetting and on the atomic structure of the phase boundary in low-pressure solution growth of GaN. Journal of Crystal Growth, 2006, 297, 133-137.	0.7	8

#	Article	IF	Citations
19	On the influence of solution density on the formation of macroscopic defects in the liquid phase epitaxy of GaN. Journal of Crystal Growth, 2008, 311, 62-65.	0.7	8
20	Vapor phase growth of GaN using GaN powder sources and thermogravimetric investigations of the evaporating behaviour of the source material. Crystal Research and Technology, 2008, 43, 14-21.	0.6	6
21	4H-SiC Homoepitaxial Growth on Substrates with Different Off-Cut Directions. Materials Science Forum, 0, 679-680, 55-58.	0.3	6
22	Influence of Epilayer Thickness and Structural Defects on the Minority Carrier Lifetime in 4H-SiC. Materials Science Forum, 0, 740-742, 633-636.	0.3	5
23	Influence and Mutual Interaction of Process Parameters on the Z_{1/2} Defect Concentration during Epitaxy of 4H-SiC. Materials Science Forum, 0, 924, 112-115.	0.3	4
24	SXRT Investigations on Electrically Stressed 4H-SiC PiN Diodes for 6.5 kV. Materials Science Forum, 0, 740-742, 899-902.	0.3	3
25	Optical in-situ monitoring system for simultaneous measurement of thickness and curvature of thick layer stacks during hydride vapor phase epitaxy growth of GaN. Journal of Crystal Growth, 2015, 427, 99-103.	0.7	3
26	Lifetime limiting defects in 4H-SiC epitaxial layers: The influence of substrate originated defects. Journal of Crystal Growth, 2021, 560-561, 126033.	0.7	3
27	Modelling of Effective Minority Carrier Lifetime in 4H-SiC n-Type Epilayers. Materials Science Forum, 0, 858, 341-344.	0.3	2
28	Optical Stressing of 4H-SiC Material and Devices. Materials Science Forum, 0, 924, 196-199.	0.3	2
29	Crystal growth of compound semiconductors with low dislocation densities. , 2008, , .		1
30	HCl Assisted Growth of Thick 4H-SiC Epilayers for Bipolar Devices. Materials Science Forum, 0, 778-780, 210-213.	0.3	1
31	Thermal Simulation of Paralleled SiC PiN Diodes in a Module Designed for 6.5 kV/1 kA. Materials Science Forum, 2015, 821-823, 616-619.	0.3	1
32	Minority Carrier Lifetime Measurements on 4H-SiC Epiwafers by Time-Resolved Photoluminescence and Microwave Detected Photoconductivity. Materials Science Forum, 2019, 963, 313-317.	0.3	0
33	Influence of Substrate Properties on the Defectivity and Minority Carrier Lifetime in 4H-SiC Homoepitaxial Layers. Materials Science Forum, 0, 963, 109-113.	0.3	0